

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

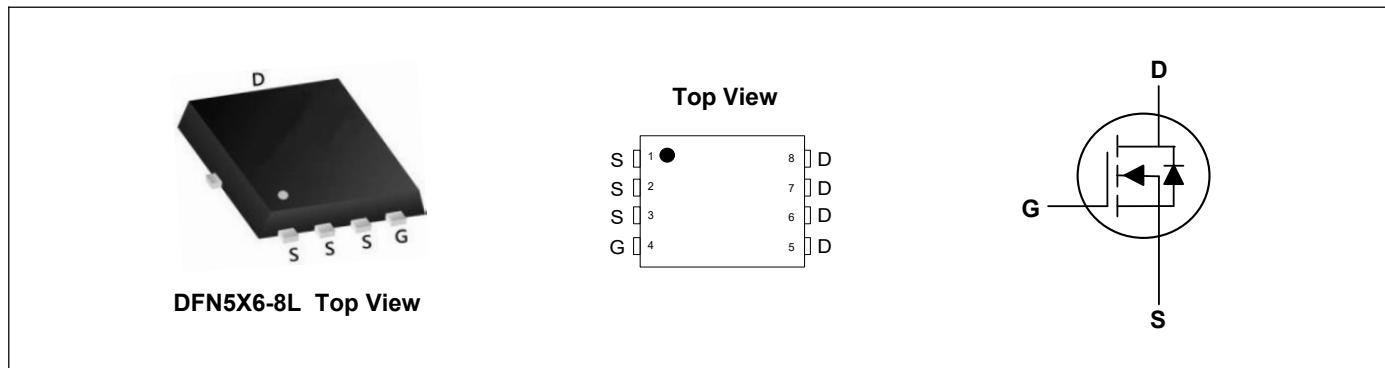
Product Summary



V_{DS}	30	V
I_D	123	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	1.5	mΩ
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	2.5	mΩ

Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	123	A
Pulsed Drain Current ²	I_{DM}	492	A
Single Pulse Avalanche Energy ³	E_{AS}	360	mJ
Total Power Dissipation	P_D	35	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	62.5	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	3.5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	30	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=30\text{A}$	---	1.25	1.5	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$, $I_D=20\text{A}$	---	2.10	2.5	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=250\mu\text{A}$	1.0	---	2.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=24\text{V}$, $V_{\text{GS}}=0\text{V}$	---	---	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Total Gate Charge	Q_g	$V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=30\text{A}$	---	51	---	nC
Gate-Source Charge	Q_{gs}		---	10	---	
Gate-Drain Charge	Q_{gd}		---	9	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=15\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_{\text{G}}=3.9\Omega$, $R_{\text{L}}=0.5\Omega$, $I_D=30\text{A}$	---	10	---	ns
Rise Time	T_r		---	83	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	51	---	
Fall Time	T_f		---	40	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	2730	---	pF
Output Capacitance	C_{oss}		---	1050	---	
Reverse Transfer Capacitance	C_{rss}		---	170	---	

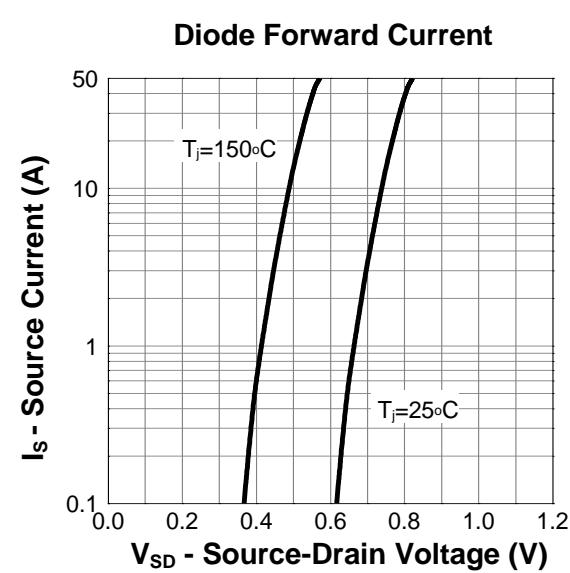
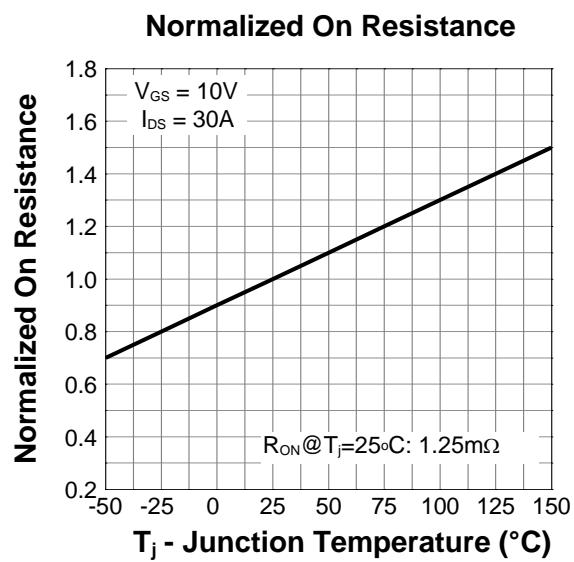
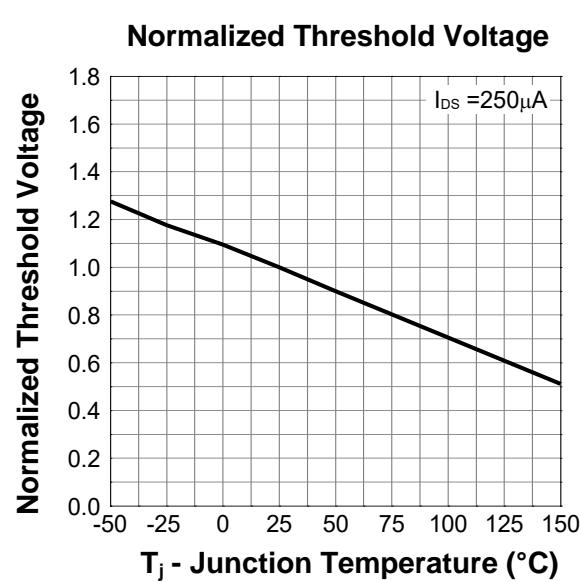
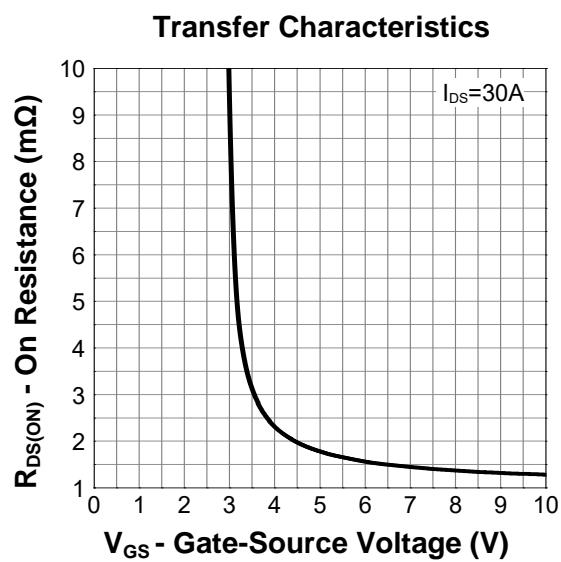
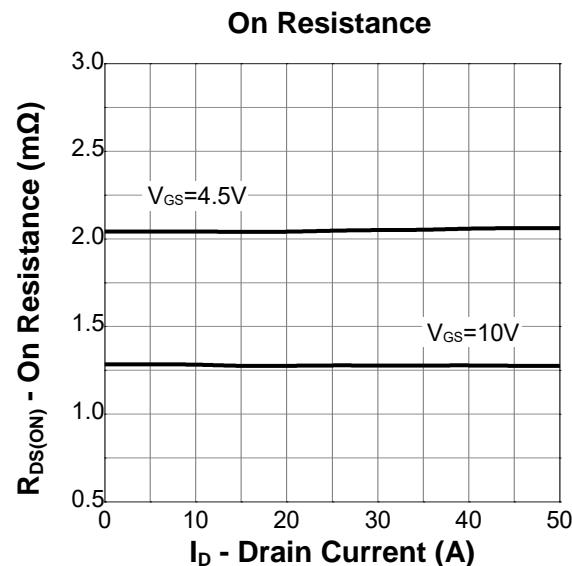
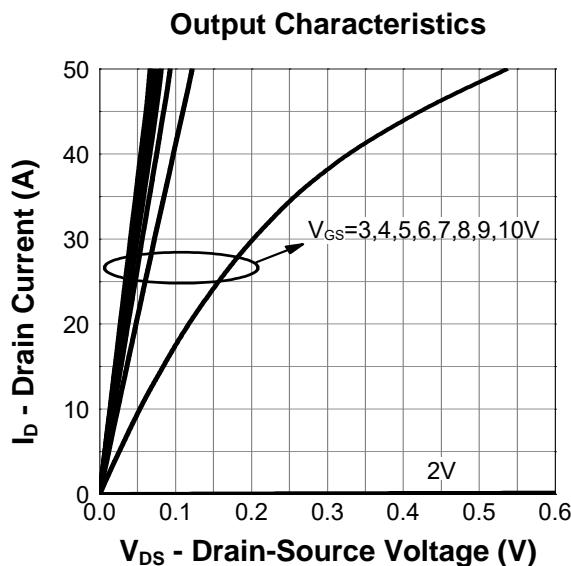
Drain-Source Diode Characteristics

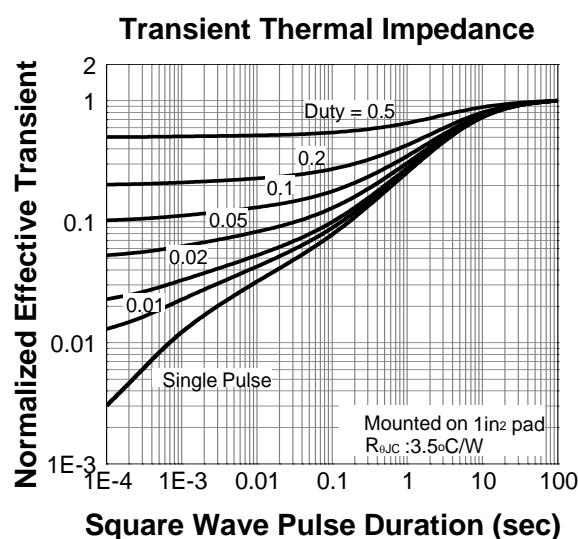
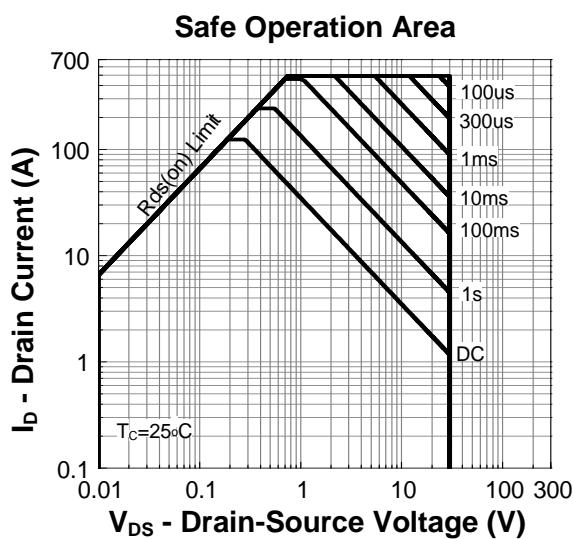
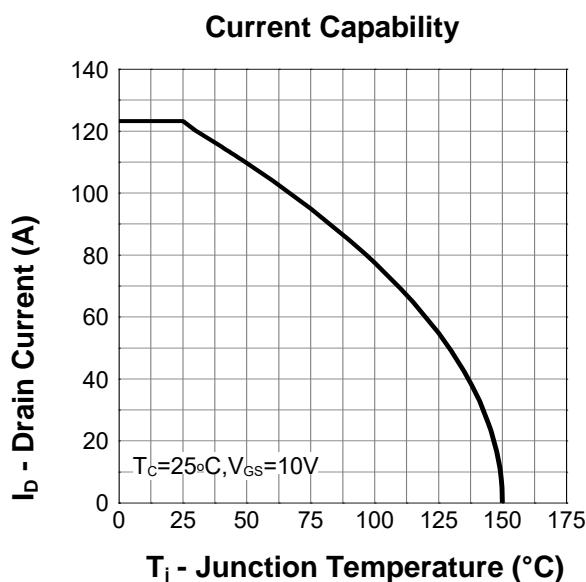
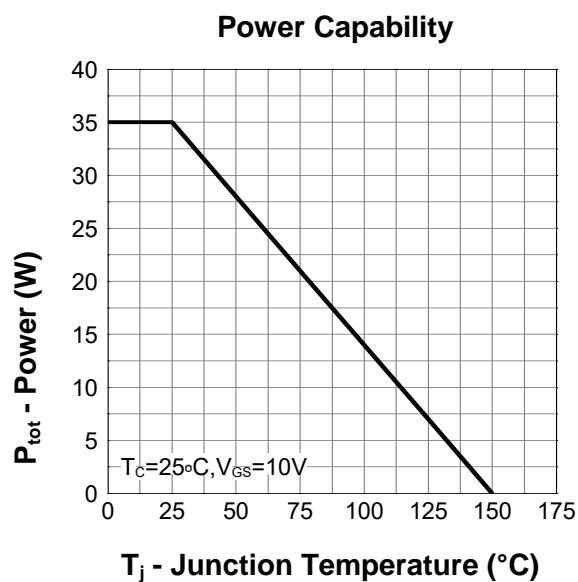
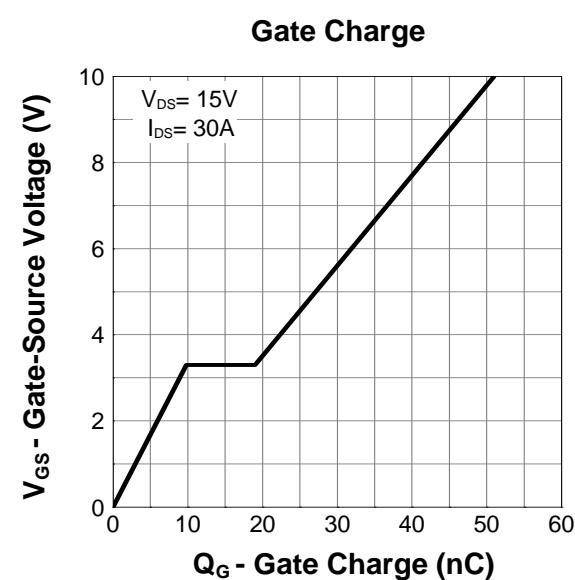
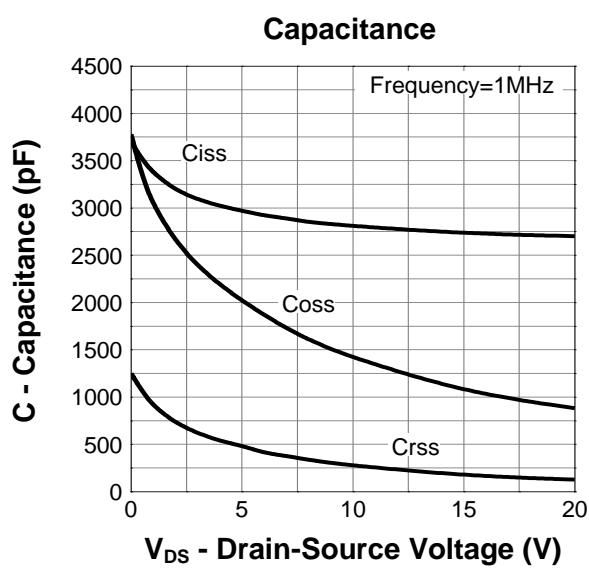
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I_s		---	---	123	A
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}$, $I_s=30\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.3	V
Reverse Recovery Time	t_{rr}	$I_F=30\text{A}$ $dI/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	38	---	nS
	Q_{rr}		---	27	---	nC

Note:

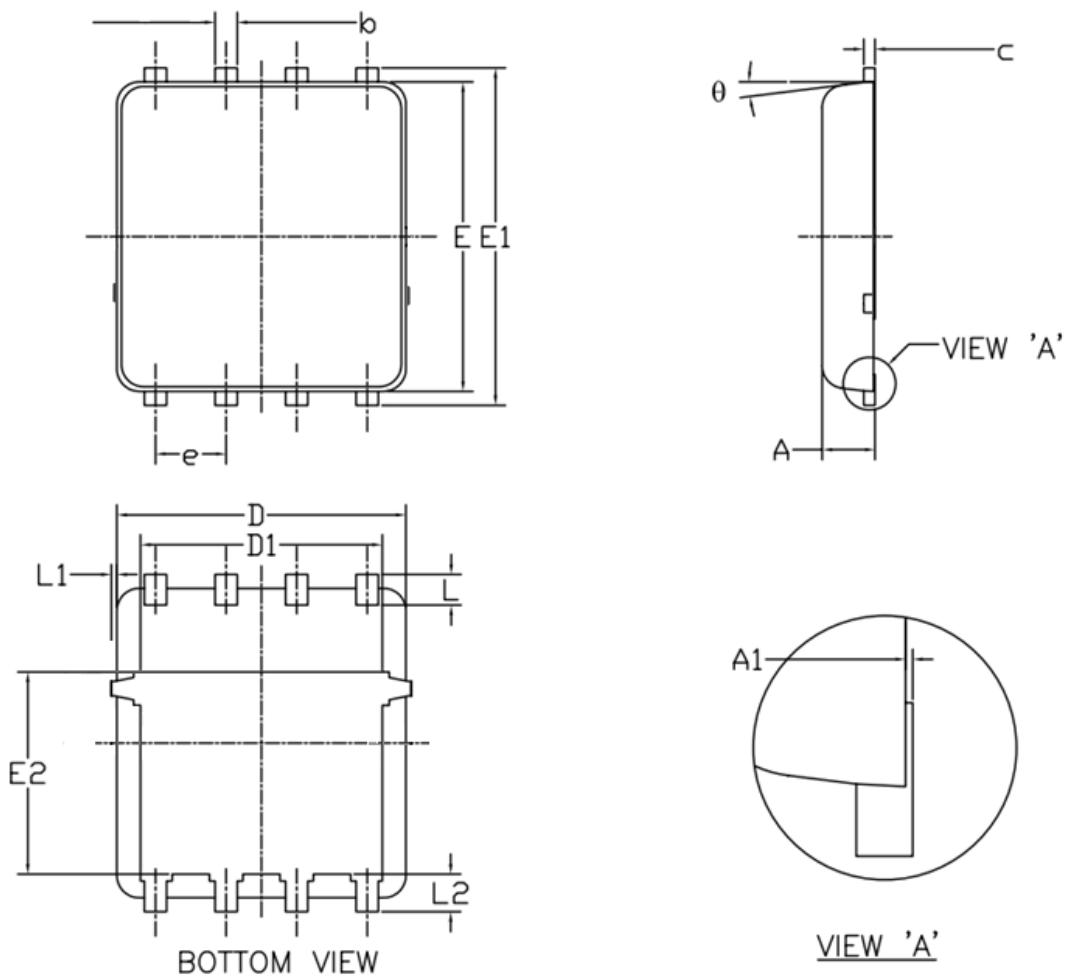
- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=30\text{V}$, $L=0.1\text{mH}$

Typical Characteristics





DFN5X6-8L Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.00	1.20	E1	5.90	6.10	6.35
A1	0.00	--	0.05	E2	3.38	3.58	3.92
b	0.30	0.40	0.51	e	1.27 BSC		
c	0.20	0.25	0.33	L	0.51	0.61	0.71
D	4.80	4.90	5.40	L1	--	--	0.15
D1	3.61	4.00	4.25	L2	0.41	0.51	0.61
E	5.65	5.80	6.06	θ	0°	--	12°